PEMH1; PUMH1

NPN/NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

Rev. 5 — 2 December 2011

Product data sheet

1. Product profile

1.1 General description

NPN/NPN double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number Package				Package	
	NXP	JEITA	complement	complement	configuration
PEMH1	SOT666	-	PEMD2	PEMB1	ultra small and flat lead
PUMH1	SOT363	SC-88	PUMD2	PUMB1	very small

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



2. Pinning information

Table 3. Pinning

Table 3.	riiiiiig		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1
			sym063

3. Ordering information

Table 4. Ordering information

Type number	Package	Package		
	Name	Description	Version	
PEMH1	-	plastic surface-mounted package; 6 leads	SOT666	
PUMH1	SC-88	plastic surface-mounted package; 6 leads	SOT363	

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
PEMH1	H2
PUMH1	H*2

[1] * = placeholder for manufacturing site code

5. Limiting values

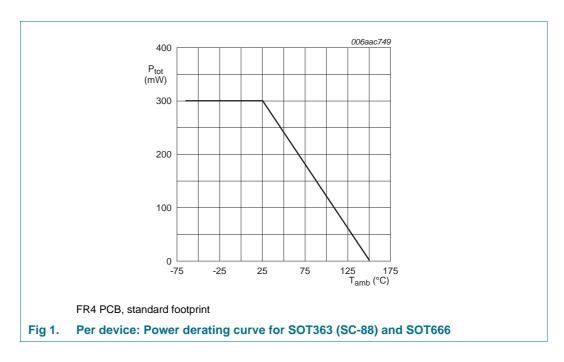
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Min	Max	Unit
stor				
collector-base voltage	open emitter	-	50	V
collector-emitter voltage	open base	-	50	V
emitter-base voltage	open collector	-	10	V
input voltage				
positive		-	+40	V
negative		-	-10	V
output current		-	100	mA
peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
PEMH1 (SOT666)		[1][2] _	200	mW
PUMH1 (SOT363)		<u>[1]</u> -	200	mW
)				
total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
PEMH1 (SOT666)		[1][2] _	300	mW
PUMH1 (SOT363)		<u>[1]</u> -	300	mW
junction temperature		-	150	°C
ambient temperature		-65	+150	°C
storage temperature		-65	+150	°C
	collector-base voltage collector-emitter voltage emitter-base voltage input voltage positive negative output current peak collector current total power dissipation PEMH1 (SOT666) PUMH1 (SOT363) total power dissipation PEMH1 (SOT666) PUMH1 (SOT363) junction temperature ambient temperature	collector-base voltage open emitter collector-emitter voltage open base emitter-base voltage open collector input voltage positive negative output current peak collector current single pulse; $t_p \le 1 \text{ ms}$ total power dissipation $T_{amb} \le 25 \text{ °C}$ PEMH1 (SOT666) PUMH1 (SOT363) total power dissipation $T_{amb} \le 25 \text{ °C}$ PEMH1 (SOT666) PUMH1 (SOT363) junction temperature ambient temperature	collector-base voltage open emitter - collector-emitter voltage open base - emitter-base voltage open collector - input voltage positive - negative - output current - peak collector current single pulse; $t_p \le 1 \text{ ms}$ total power dissipation $T_{amb} \le 25 \text{ °C}$ PEMH1 (SOT666) PUMH1 (SOT363) [1] - total power dissipation $T_{amb} \le 25 \text{ °C}$ PEMH1 (SOT666) [1][2] - PUMH1 (SOT363) [1] - include temperature - collector emitter open emitter - collector -	collector-base voltage open emitter - 50 collector-emitter voltage open base - 50 emitter-base voltage open collector - 10 input voltage positive - +40 negative10 output current - 100 peak collector current single pulse; - 100 total power dissipation $T_{amb} \le 25 ^{\circ}\text{C}$ PEMH1 (SOT666) [1][2] - 200 PUMH1 (SOT363) [1] - 300 punction temperature - 150 ambient temperature - 150 ambient temperature - 65 +150

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.



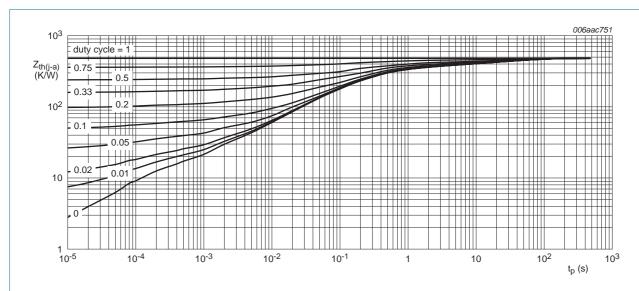
6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMH1 (SOT666)		[1][2]	-	625	K/W
	PUMH1 (SOT363)		<u>[1]</u> _	-	625	K/W
Per device	9					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMH1 (SOT666)		[1][2] -	-	417	K/W
	PUMH1 (SOT363)		<u>[1]</u> _	-	417	K/W

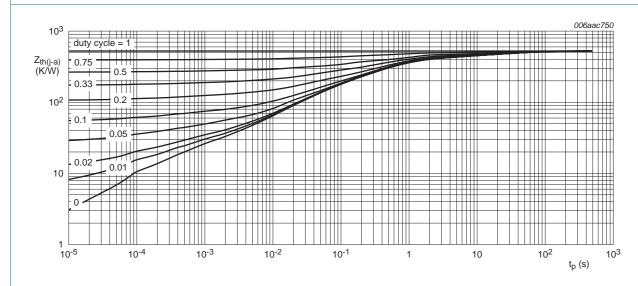
^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.



FR4 PCB, standard footprint

Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PEMH1 (SOT666); typical values



FR4 PCB, standard footprint

Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PUMH1 (SOT363); typical values

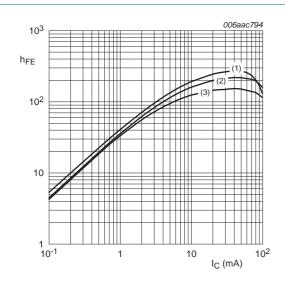
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO} collec	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	100	mA
	current	$V_{CE} = 30 \text{ V; } I_{B} = 0 \text{ A;}$ $T_{j} = 150 \text{ °C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	180	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	60	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	1.1	0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 5 \text{ mA}$	2.5	1.7	-	V
R1	bias resistor 1 (input)		15.4	22	28.6	$k\Omega$
R2/R1	bias resistor ratio		8.0	1	1.2	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz	1] _	230	-	MHz

^[1] Characteristics of built-in transistor



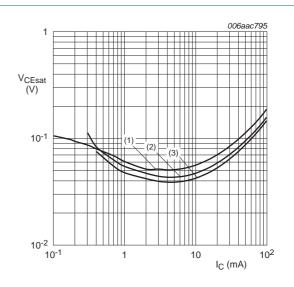
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 4. DC current gain as a function of collector current; typical values



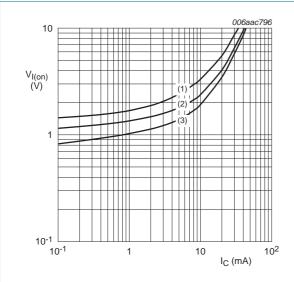
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



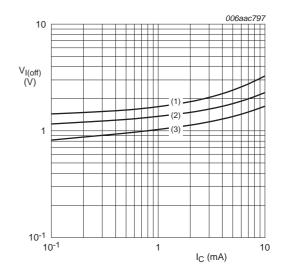
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. On-state input voltage as a function of collector current; typical values



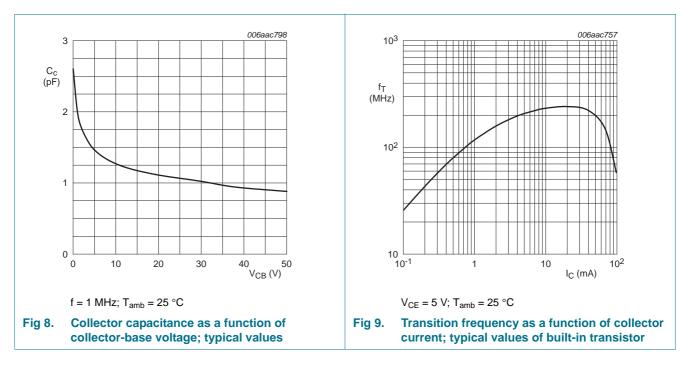
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 7. Off-state input voltage as a function of collector current; typical values

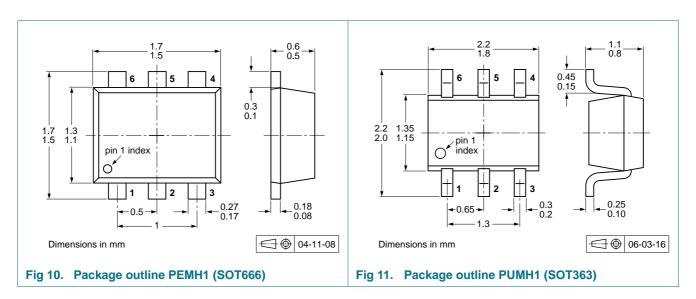


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



PEMH1_PUMH1

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10. Packing information

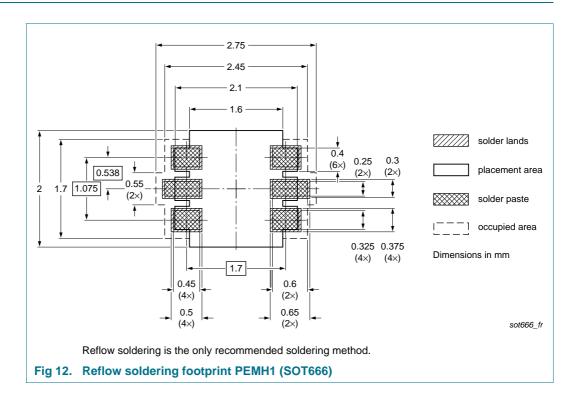
Table 9. Packing methods

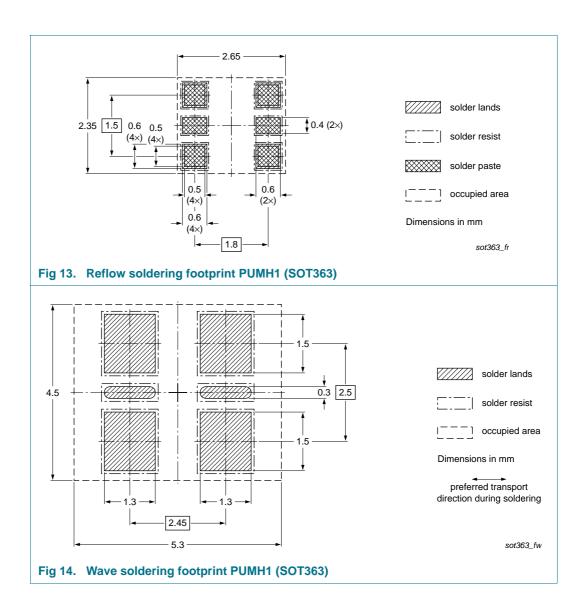
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type F number	Package	Description	Pac	king	quanti	ty	
				0 4	000	8000	10000
PEMH1 SOT666	2 mm pitch, 8 mm tape and reel	-	-		-315	-	
		4 mm pitch, 8 mm tape and reel	-		115	-	-
PUMH1	SOT363	4 mm pitch, 8 mm tape and reel; T1	-115	-		-	-135
		4 mm pitch, 8 mm tape and reel; T2	-125	5 -		-	-165

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering





12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
PEMH1_PUMH1 v.5	20111202	Product data sheet	-	PEMH1_PUMH1 v.4			
Modifications:		of this document has been of NXP Semiconductors.	redesigned to comply w	rith the new identity			
	 Legal texts have been adapted to the new company name where appropriate. 						
	Section 1 "Product profile": updated						
	Section 4 "Marking": updated						
	• Figure 1 to 9: added						
	Section 6 "Thermal characteristics": updated						
	 Table 8 "Characteristics": V_{i(on)} redefined to V_{I(on)} on-state input voltage, V_{i(off)} redefined to V_{I(off)} off-state input voltage, I_{CEO} updated, f_T added 						
	Section 8 "Test information": added						
	 Section 9 "Package outline": superseded by minimized package outline drawings 						
	Section 10 "Packing information": added						
	Section 11 "Soldering": added						
	 Section 13 	"Legal information": updated	i				
PEMH1_PUMH1 v.4	20031008	Product data sheet	-	PEMH1 v.1			
				PUMH1 v.3			
PEMH1 v.1	20011022	Preliminary specification	-	-			
PUMH1 v.3	19990520	Product specification	-	PUMH1 v.2			
PUMH1 v.2	19980806	Product specification	-	PUMH1 v.1			
PUMH1 v.1	19971212	Product specification	-	-			

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PEMH1_PUMH1

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PEMH1; PUMH1

NPN/NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

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PEMH1; PUMH1

NPN/NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

15. Contents

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